1N5614 - 1N5622

GLASS PASSIVATED JUNCTION SILICON RECTIFIERS

PRV : 200 - 1000 Volts
Io : 1.0 Ampere

FEATURES :

* Glass passivated chip
* High forward surge current capability
* High reliability
* Low reverse current
* Low forward voltage drop
* Pb / RoHS Free

MECHANICAL DATA :

* Case : DO-41 Molded plastic
* Epoxy : UL94V-O rate flame retardant
* Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
* Polarity : Color band denotes cathode end
* Mounting position : Any
* Weight : 0.34 gram

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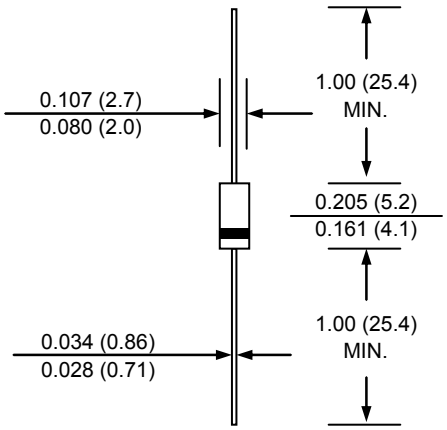

Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

RATING	SYMBOL	1N5614	1N5616	1N5618	1N5620	1N5622	UNIT
Maximum Working Peak Reverse Voltage	V_{RWM}	200	400	600	800	1000	V
Minimum Breakdown Voltage @ 50 µA	$V_{BR(MIN)}$	220	440	660	880	1100	V
Maximum Average Forward Current at Ta = 55 °C	$I_{F(AV)}$	1.0					A
at Ta = 100 °C		0.75					
Peak Forward Surge Current (Ta = 100 °C,f = 60 Hz, $I_{F(AV)}$ = 750 mA for ten 8.3 ms surges @ 1 minute intervals)	I_{FSM}	30					A
Minimum Forward Voltage at I_F = 3.0 A	$V_{F(MIN)}$	0.8					V
Maximum Forward Voltage at I_F = 3.0A	$V_{F(MAX)}$	1.3					V
Maximum Reverse Current at V_{RWM}, Ta = 25 °C	I_R	0.5					µA
at V_{RWM}, Ta = 100 °C	$I_{R(H)}$	25					
Maximum Reverse Recovery Time (Note 1)	Trr	2.0					µs
Thermal Resistance , Junction to Lead (Note 2)	$R_{\Theta JL}$	38					°C/W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-65 to +175					°C

Notes :

(1) Reverse Recovery Test Conditions : I_F = 0.5 A, I_{RM} = 1.0 A, $I_{R(REC)}$ = 0.25 A.

(2) At 3/8"(10 mm) lead length form body.